



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of
Bojarczuk, et al.

Serial No.: 09/755,164

Filed: January 8, 2001

Group Art Unit: 2826

Examiner:

Quinto, Kevin V.

For: ALUMINUM NITRIDE AND ALUMINUM OXIDE/ALUMINUM NITRIDE
HETEROSTRUCTURE GATE DIELECTRIC STACK BASED FIELD EFFECT
TRANSISTORS AND METHOD FOR FORMING SAME

Honorable Commissioner of Patents
Washington, D.C. 20231

TECHNOLOGY CENTER 2800

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Amend
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AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated July 3, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1-7, 11, 15 and 17 as follows:

(Amended) A field effect transistor, comprising:
a substrate comprising a source region, a drain region, and a channel region therebetween;
an insulating layer disposed over said channel region, said insulating layer comprising a
layer comprising aluminum nitride and at least one of a layer of aluminum oxide, a layer of
silicon dioxide, and a layer of silicon nitride disposed over said channel region; and
a gate electrode disposed over said insulating layer.

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